

DESCRIPTION

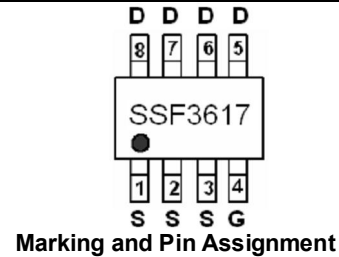
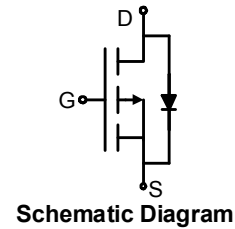
The SSF3617 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

- $V_{DS} = -30V, I_D = -10A$
 $R_{DS(ON)} < 35m\Omega @ V_{GS} = -4.5V$
 $R_{DS(ON)} < 18m\Omega @ V_{GS} = -10V$
- High Power and current handling capability
- Lead free product
- Surface Mount Package

APPLICATIONS

- PWM applications
- Load switch
- Power management



PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape Width	Quantity
SSF3617	SSF3617	SOP-8	Ø330mm	12mm	3000 units

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 25	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	$I_D(25^\circ C)$	-10	A
	$I_D(70^\circ C)$	-8	A
	I_{DM}	-80	A
Maximum Power Dissipation	P_D	3.1	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	75	$^\circ C/W$
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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30V, V_{GS} = 0V$			-1	μA

Gate-Body Leakage Current	I _{GSS}	V _{GS} =±25V, V _{DS} =0V			±100	nA
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1.7	-2.2	-3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-7.5A		24	35	mΩ
		V _{GS} =-10V, I _D =-10A		14	18	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-10A		20		S
DYNAMIC CHARACTERISTICS (Note4)						
Input Capacitance	C _{ISS}	V _{DS} =-15V, V _{GS} =0V, F=1.0MHz		1200		PF
Output Capacitance	C _{OSS}			240		PF
Reverse Transfer Capacitance	C _{rSS}			150		PF
SWITCHING CHARACTERISTICS (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DS} =-15V, V _{GS} =-10V, R _{GEN} =3Ω I _D =1A		9		nS
Turn-on Rise Time	t _r			8.5		nS
Turn-Off Delay Time	t _{d(off)}			20		nS
Turn-Off Fall Time	t _f			8		nS
Total Gate Charge	Q _g	V _{DS} =-15V, I _D =-10A, V _{GS} =-10V		18		nC
Gate-Source Charge	Q _{gs}			5		nC
Gate-Drain Charge	Q _{gd}			3.5		nC
Body Diode Reverse Recovery Time	T _{rr}	I _F =-10A, dI/dt=100A/μs		24		nS
Body Diode Reverse Recovery Charge	Q _{rr}			12		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-1A		-0.74	-1	V

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on 1in² FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

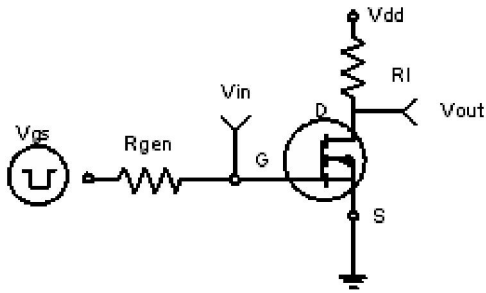


Figure 1: Switching Test Circuit

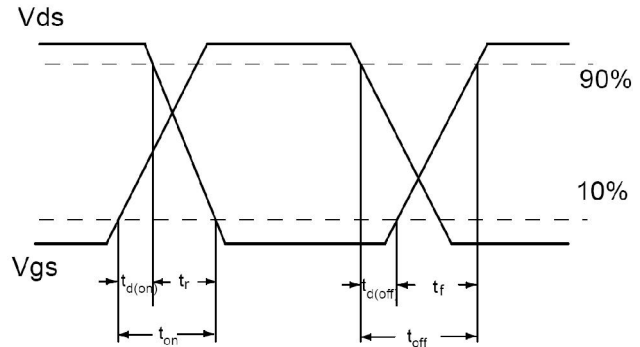


Figure 2: Switching Waveform

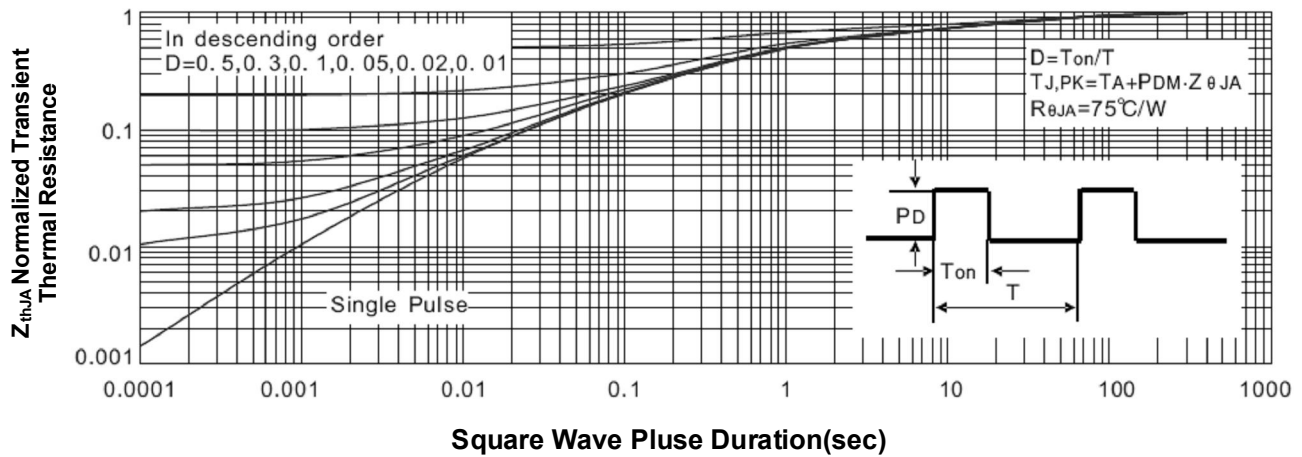
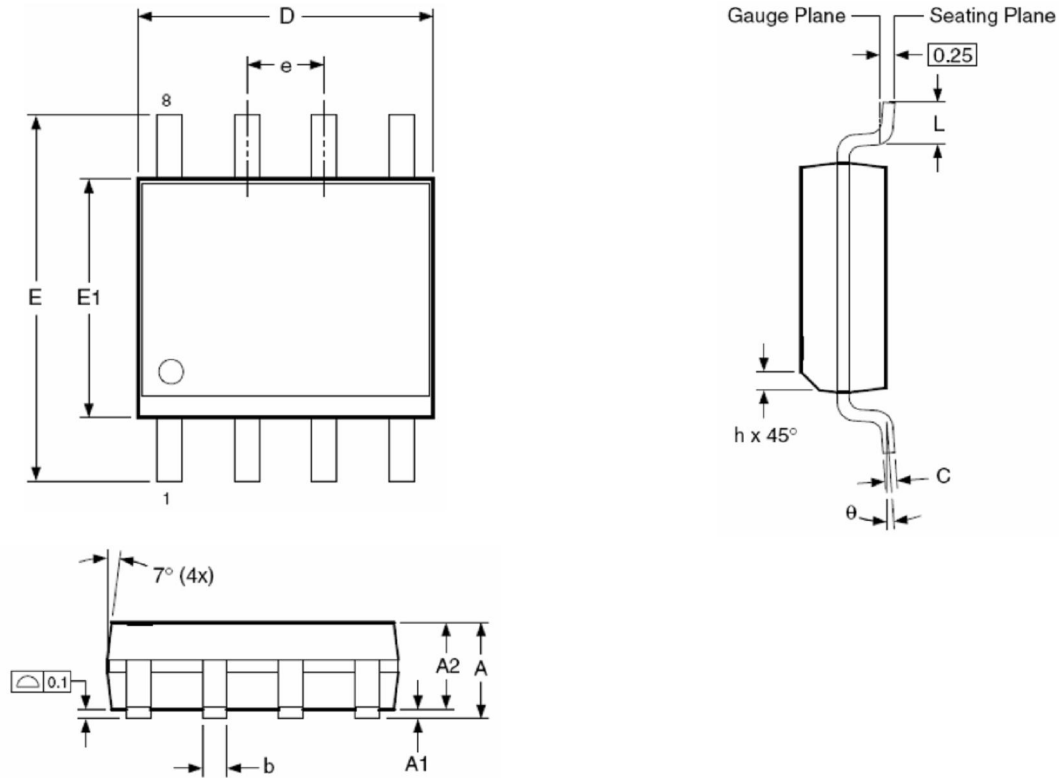
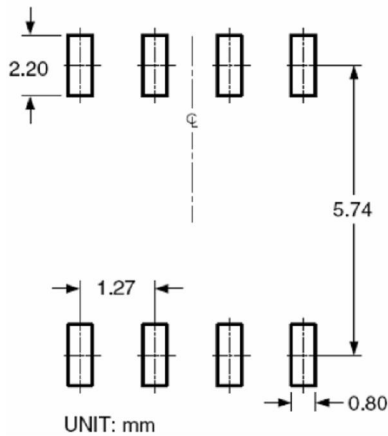


Figure 3 Normalized Maximum Transient Thermal Impedance

SOP-8 PACKAGE INFORMATION



RECOMMENDED LAND PATTERN



Dimensions in millimeters

Symbols	Min.	Nom.	Max.
A	1.35	1.65	1.75
A1	0.10	—	0.25
A2	1.25	1.50	1.65
b	0.31	—	0.51
c	0.17	—	0.25
D	4.80	4.90	5.00
E1	3.80	3.90	4.00
e	1.27 BSC		
E	5.80	6.00	6.20
h	0.25	—	0.50
L	0.40	—	1.27
θ	0°	—	8°

Dimensions in inches

Symbols	Min.	Nom.	Max.
A	0.053	0.065	0.069
A1	0.004	—	0.010
A2	0.049	0.059	0.065
b	0.012	—	0.020
c	0.007	—	0.010
D	0.189	0.193	0.197
E1	0.150	0.154	0.157
e	0.050 BSC		
E	0.228	0.236	0.244
h	0.010	—	0.020
L	0.016	—	0.050
θ	0°	—	8°

NOTES:

1. Dimensions are inclusive of plating
2. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 6 mils.
3. Dimension L is measured in gauge plane.
4. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.